

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3821	(ion adj (implanting or implant or implanted or implantation)) same (angle or angled or tilted or sloped or oblique)	US-PGPUB; USPAT	OR	ON	2005/05/23 10:16
L2	2263	1 and width	US-PGPUB; USPAT	OR	ON	2005/05/23 10:03
L3	478	(dopant with concentration) and 2	US-PGPUB; USPAT	OR	ON	2005/05/23 10:31
L6	35	3 and (transmission or transmissive)	US-PGPUB; USPAT	OR	ON	2005/05/23 10:32
L7	1611	(ion adj (implanting or implant or implanted or implantation)) same (angle or angled or tilted or sloped or oblique)	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 10:16
L8	30	(dopant with concentration) and 7	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 10:17
L10	800	(dopant with concentration) and 1	US-PGPUB; USPAT	OR	ON	2005/05/23 10:31
L11	56	10 and (transmission or transmissive)	US-PGPUB; USPAT	OR	ON	2005/05/23 10:32
L12	21	11 not 6	US-PGPUB; USPAT	OR	ON	2005/05/23 10:32
L13	3	((("20020019103") or ("20020036328") or ("20020005553")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/23 10:46
L14	15	((("4042843") or ("5372957") or ("6281558") or ("6020244") or ("5841170") or ("6297098") or ("6524903") or ("4315781") or ("5362981") or ("5589410") or ("5827763") or ("6187619") or ("6153454") or ("5817551") or ("6163053")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/23 10:52
L15	1	("6020244").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/23 10:52

PAT-NO: JP02000091350A

DOCUMENT-IDENTIFIER: JP 2000091350 A

TITLE: MANUFACTURE OF SEMICONDUCTOR FIELD EFFECT  
TRANSISTOR

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Abstract Text - FPAR (1):

PROBLEM TO BE SOLVED: To form a plurality of doped regions in a drain region and a source region and to set the increase of the number of processes to be minimum by only changing the angle of ion implantation at oblique ion implantation.

Abstract Text - FPAR (2):

SOLUTION: A T-type dummy gate 24 is formed on a semiconductor substrate 1, and ions are implanted on the surface of the substrate from an obliquely upper part for plural times at different angles. An insulating film 21 of the T-type dummy gate 24 has a thickness which prevents the transmission of the ions at implanting of the ions. Dopant concentration and the implantation depth of dopant are decided by the angle at the time of implanting the ions. Thus, the regions depod in several stages can be formed in a drain, and the increase of the number of processes can be suppressed to a minimum only by changing the conditions at implanting of the ions.